

## Excellent Integrated System Limited

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[Everspin Technologies Inc.](#)  
[MR0A08BCYS35](#)

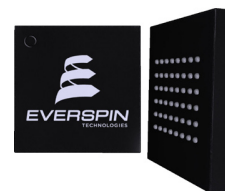
For any questions, you can email us directly:

[sales@integrated-circuit.com](mailto:sales@integrated-circuit.com)

## FEATURES

- 3.3 Volt power supply
- Fast 35 ns read/write cycle
- SRAM compatible timing
- Native non-volatility
- Unlimited read & write endurance
- Data always non-volatile for >20 years at temperature
- Commercial and industrial temperatures
- All products meet MSL-3 moisture sensitivity level
- RoHS-Compliant TSOP2 and BGA packages

128K x 8 MRAM



48-ball FBGA



44-pin TSOP2

## BENEFITS

- One memory replaces FLASH, SRAM, EEPROM and MRAM in system for simpler, more efficient design
- Improves reliability by replacing battery-backed SRAM

## INTRODUCTION

The **MR0A08B** is a 1,048,576-bit magnetoresistive random access memory (MRAM) device organized as 131,072 words of 8 bits. The MR0A08B offers SRAM compatible 35 ns read/write timing with unlimited endurance.

Data is always non-volatile for greater than 20-years. Data is automatically protected on power loss by low-voltage inhibit circuitry to prevent writes with voltage out of specification. The MR0A08B is the ideal memory solution for applications that must permanently store and retrieve critical data and programs quickly.

The **MR0A08B** is available in small footprint 400-mil, 44-lead plastic small-outline TSOP type-2 package, 8 mm x 8 mm, or a 48-pin ball grid array (BGA) package with 0.75 mm ball centers. (The 32-SOIC package options is obsolete and no longer available for new orders.) These packages are compatible with similar low-power SRAM products and other non-volatile RAM products.

The **MR0A08B** provides highly reliable data storage over a wide range of temperatures. The product is offered with commercial temperature range (0 to +70 °C) and industrial temperature range (-40 to +85 °C).



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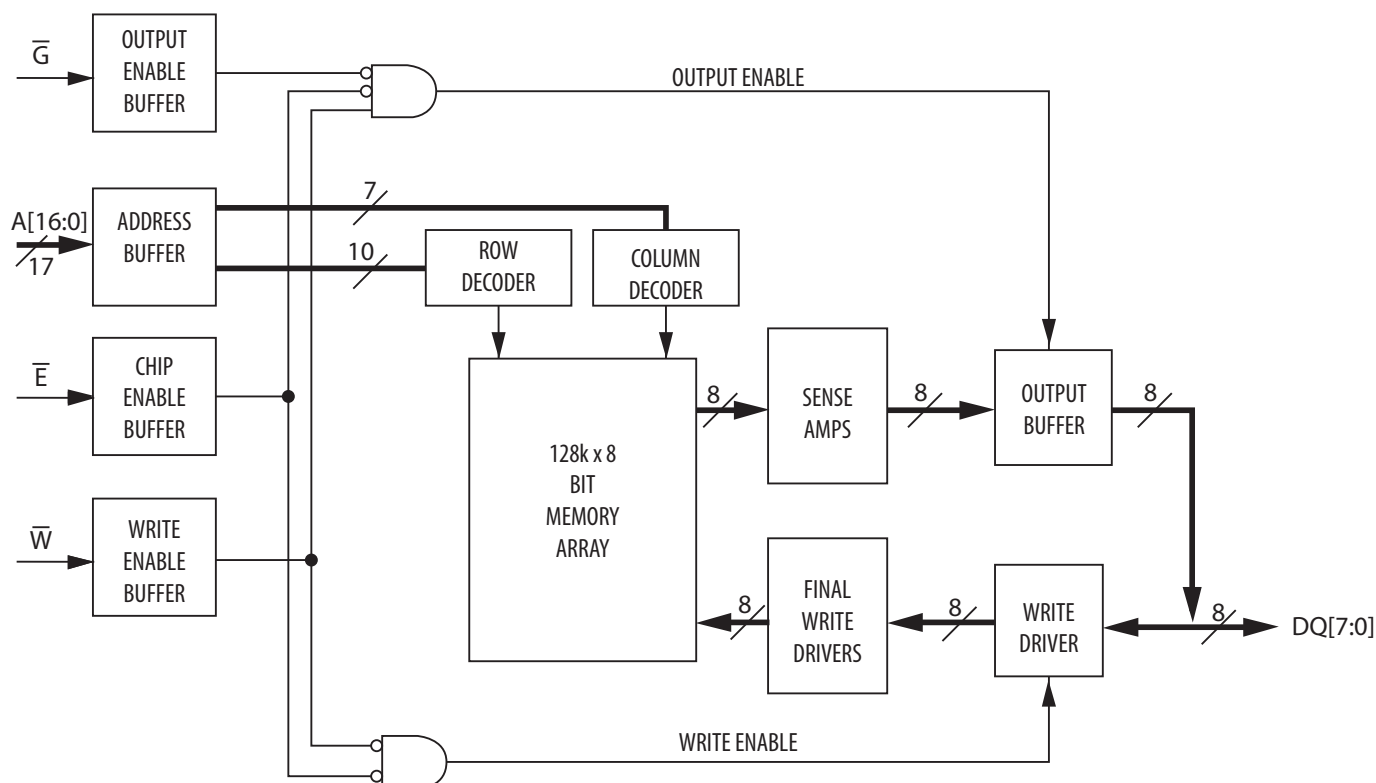
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## BLOCK DIAGRAM AND PIN ASSIGNMENTS

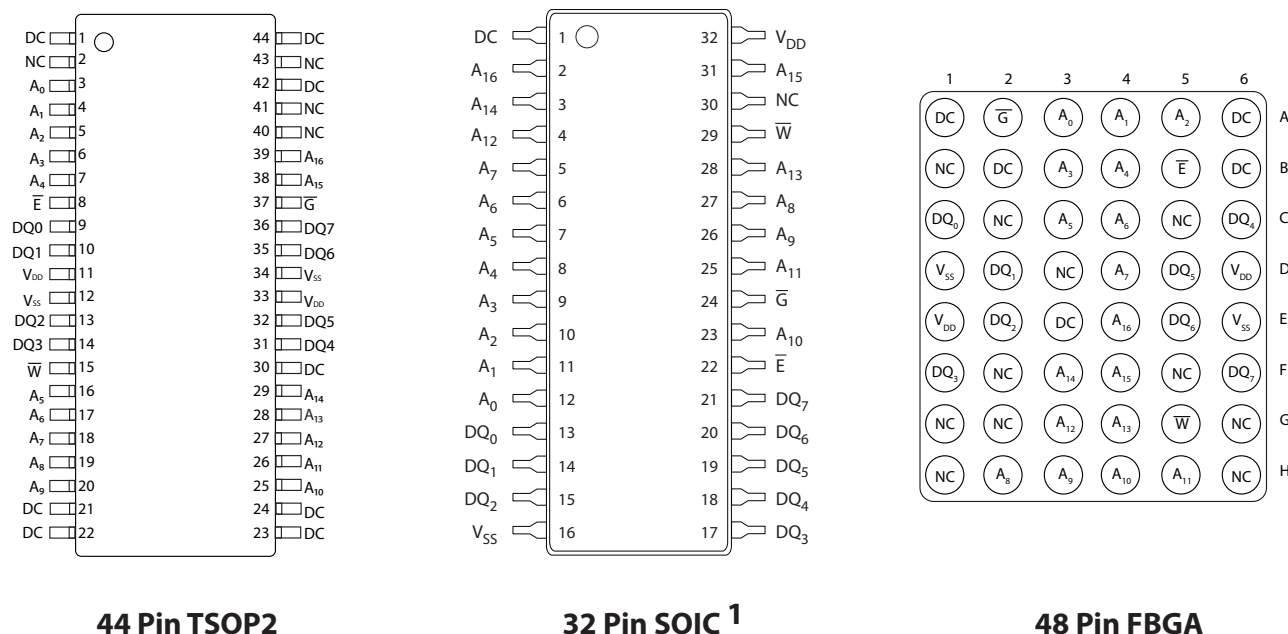
**Figure 1 – MR0A08B Block Diagram**



**Table 1 – Pin Functions**

Signal Name	Function
A	Address Input
$\overline{E}$	Chip Enable
$\overline{W}$	Write Enable
$\overline{G}$	Output Enable
DQ	Data I/O
$V_{DD}$	Power Supply
$V_{SS}$	Ground
DC	Do Not Connect
NC	No Connection - Pin 2, 40, 41, 43 (TSOP2); Ball C2, C5, D3, F2, F5, G1, G2, G6, H1, H6 (BGA); Pin 30 (SOIC) Reserved For Future Expansion

**Figure 2 – Pin Diagrams for Available Packages (Top View) <sup>1</sup>**



Note:

1. The 32-SOIC package is obsolete and shown for legacy reference only. This package option is no longer available for new orders.

## OPERATING MODES

**Table 2 – Operating Modes**

$\bar{E}$ <sup>1</sup>	$\bar{G}$ <sup>1</sup>	$\bar{W}$ <sup>1</sup>	Mode	$V_{DD}$ Current	DQ[7:0] <sup>2</sup>
H	X	X	Not selected	$I_{SB1}, I_{SB2}$	Hi-Z
L	H	H	Output disabled	$I_{DDR}$	Hi-Z
L	L	H	Byte Read	$I_{DDR}$	$D_{Out}$
L	X	L	Byte Write	$I_{DDW}$	$D_{in}$

Notes:

1. H = high, L = low, X = don't care
2. Hi-Z = high impedance

## ELECTRICAL SPECIFICATIONS

### Absolute Maximum Ratings

This device contains circuitry to protect the inputs against damage caused by high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage greater than maximum rated voltages to these high-impedance (Hi-Z) circuits.

The device also contains protection against external magnetic fields. Precautions should be taken to avoid application of any magnetic field more intense than the maximum field intensity specified in the maximum ratings. <sup>1</sup>

**Table 3 – Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit
Supply voltage <sup>2,3</sup>	$V_{DD}$	-0.5 to 4.0	V
Voltage on any pin <sup>2,3</sup>	$V_{IN}$	-0.5 to $V_{DD} + 0.5$	V
Output current per pin	$I_{OUT}$	±20	mA
Package power dissipation <sup>3</sup>	$P_D$	0.600	W
Temperature under bias MR0A08B (Commercial) MR0A08BC (Industrial)	$T_{BIAS}$	-10 to 85 -45 to 95	°C
Storage Temperature	$T_{stg}$	-55 to 150	°C
Lead temperature during solder (3 minute max)	$T_{Lead}$	260	°C
Maximum magnetic field during write MR0A08B (All Temperatures)	$H_{max\_write}$	2000	A/m
Maximum magnetic field during read or standby	$H_{max\_read}$	8000	A/m

Notes:

1. Permanent device damage may occur if absolute maximum ratings are exceeded. Functional operation should be restricted to recommended operating conditions. Exposure to excessive voltages or magnetic fields could affect device reliability.
2. All voltages are referenced to  $V_{SS}$ .
3. Power dissipation capability depends on package characteristics and use environment.

## OPERATING CONDITIONS

**Table 4 – Operating Conditions**

Parameter	Symbol	Min	Typical	Max	Unit
Power supply voltage	$V_{DD}$	3.0 <sup>1</sup>	3.3	3.6	V
Write inhibit voltage	$V_{WI}$	2.5	2.7	3.0 <sup>1</sup>	V
Input high voltage	$V_{IH}$	2.2	-	$V_{DD} + 0.3$ <sup>2</sup>	V
Input low voltage	$V_{IL}$	-0.5 <sup>3</sup>	-	0.8	V
Temperature under bias					
MR0A08B (Commercial)	$T_A$	0		70	°C
MR0A08BC (Industrial)		-40		85	

Notes:

1. There is a 2 ms startup time once  $V_{DD}$  exceeds  $V_{DD, (max)}$ . See “Figure 3 – Power Up and Power Down Diagram”.
2.  $V_{IH} (max) = V_{DD} + 0.3 V_{DC}$ ;  $V_{IH} (max) = V_{DD} + 2.0 V_{AC}$  (pulse width  $\leq 10$  ns) for  $I \leq 20.0$  mA.
3.  $V_{IL} (min) = -0.5 V_{DC}$ ;  $V_{IL} (min) = -2.0 V_{AC}$  (pulse width  $\leq 10$  ns) for  $I \leq 20.0$  mA.



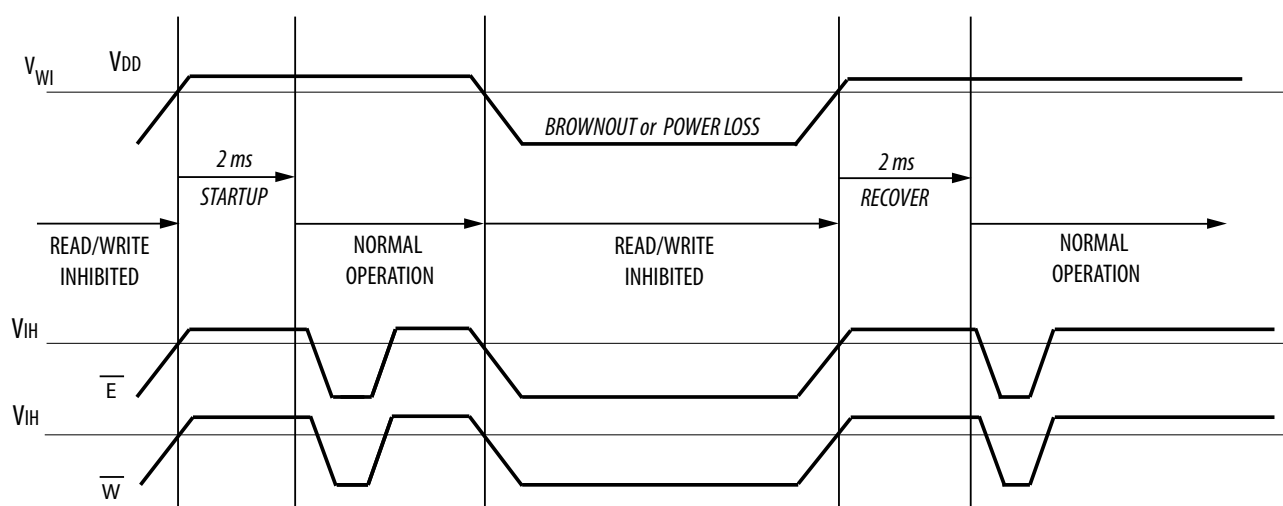
## Power Up and Power Down Sequencing

The MRAM is protected from write operations whenever  $V_{DD}$  is less than  $V_{WI}$ . As soon as  $V_{DD}$  exceeds  $V_{DD}(\min)$ , there is a startup time of 2 ms before read or write operations can start. This time allows memory power supplies to stabilize.

The  $\bar{E}$  and  $\bar{W}$  control signals should track  $V_{DD}$  on power up to  $V_{DD} - 0.2\text{ V}$  or  $V_{IH}$  (whichever is lower) and remain high for the startup time. In most systems, this means that these signals should be pulled up with a resistor so that signal remains high if the driving signal is Hi-Z during power up. Any logic that drives  $\bar{E}$  and  $\bar{W}$  should hold the signals high with a power-on reset signal for longer than the startup time.

During power loss or brownout where  $V_{DD}$  goes below  $V_{WI}$ , writes are protected and a startup time must be observed when power returns above  $V_{DD}(\min)$ .

**Figure 3 – Power Up and Power Down Diagram**



## DC CHARACTERISTICS

**Table 5 – DC Characteristics**

Parameter	Symbol	Min	Typical	Max	Unit
Input leakage current	$I_{lkg(I)}$	-	-	$\pm 1$	$\mu A$
Output leakage current	$I_{lkg(O)}$	-	-	$\pm 1$	$\mu A$
Output low voltage ( $I_{OL} = +4 \text{ mA}$ ) ( $I_{OL} = +100 \mu A$ )	$V_{OL}$	-	-	0.4 $V_{SS} + 0.2$	V
Output high voltage ( $I_{OL} = -4 \text{ mA}$ ) ( $I_{OL} = -100 \mu A$ )	$V_{OH}$	2.4 $V_{DD} - 0.2$	-	-	V

**Table 6 – Power Supply Characteristics**

Parameter	Symbol	Typical	Max	Unit
AC active supply current - read modes <sup>1</sup> ( $I_{OUT} = 0 \text{ mA}$ , $V_{DD} = \text{max}$ )	$I_{DDR}$	25	30	mA
AC active supply current - write modes <sup>1</sup> ( $V_{DD} = \text{max}$ ) MR0A08B (Commercial) MR0A08BC (Industrial)	$I_{DDW}$	55 55	65 70	mA
AC standby current ( $V_{DD} = \text{max}$ , $\bar{E} = V_{IH}$ ) <i>no other restrictions on other inputs</i>	$I_{SB1}$	6	7	mA
CMOS standby current ( $\bar{E} \geq V_{DD} - 0.2 \text{ V}$ and $V_{In} \leq V_{SS} + 0.2 \text{ V}$ or $\geq V_{DD} - 0.2 \text{ V}$ ) ( $V_{DD} = \text{max}$ , $f = 0 \text{ MHz}$ )	$I_{SB2}$	5	6	mA

Notes:

1. All active current measurements are measured with one address transition per cycle and at minimum cycle time.

## TIMING SPECIFICATIONS

**Table 7 – Capacitance**

Parameter <sup>1</sup>	Symbol	Typical	Max	Unit
Address input capacitance	$C_{In}$	-	6	pF
Control input capacitance	$C_{In}$	-	6	pF
Input/Output capacitance	$C_{I/O}$	-	8	pF

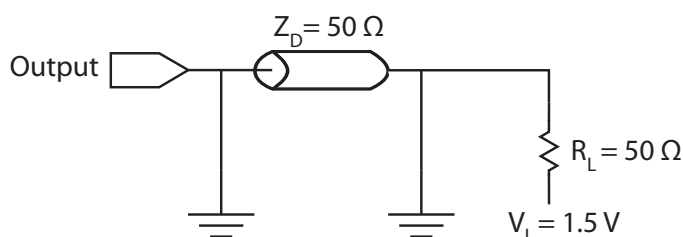
Notes:

1.  $f = 1.0 \text{ MHz}$ ,  $dV = 3.0 \text{ V}$ ,  $T_A = 25^\circ\text{C}$ , periodically sampled rather than 100% tested.

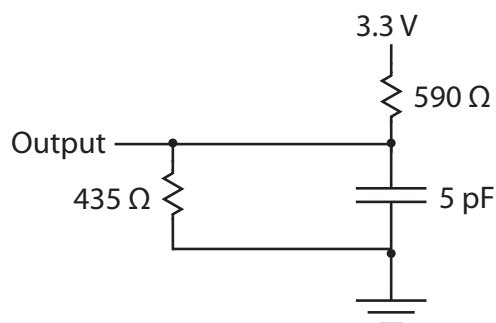
**Table 8 – AC Measurement Conditions**

Parameter	Value	Unit
Logic input timing measurement reference level	1.5	V
Logic output timing measurement reference level	1.5	V
Logic input pulse levels	0 or 3.0	V
Input rise/fall time	2	ns
Output load for low and high impedance parameters	See Figure 4	
Output load for all other timing parameters	See Figure 5	

**Figure 4 – Output Load Test Low and High**



**Figure 5 – Output Load Test All Others**



## Read Mode

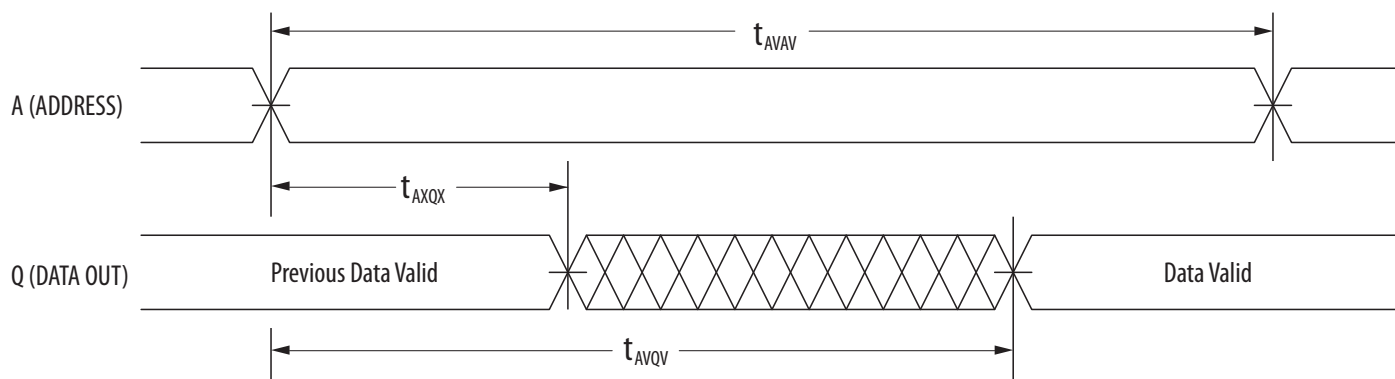
**Table 9 – Read Cycle Timing**

Parameter <sup>1</sup>	Symbol	Min	Max	Unit
Read cycle time	t <sub>AVAV</sub>	35	-	ns
Address access time	t <sub>AVQV</sub>	-	35	ns
Enable access time <sup>2</sup>	t <sub>ELQV</sub>	-	35	ns
Output enable access time	t <sub>GLQV</sub>	-	15	ns
Output hold from address change	t <sub>AXQX</sub>	3	-	ns
Enable low to output active <sup>3</sup>	t <sub>ELQX</sub>	3	-	ns
Output enable low to output active <sup>3</sup>	t <sub>GLQX</sub>	0	-	ns
Enable high to output Hi-Z <sup>3</sup>	t <sub>EHQZ</sub>	0	15	ns
Output enable high to output Hi-Z <sup>3</sup>	t <sub>GHQZ</sub>	0	10	ns

Notes:

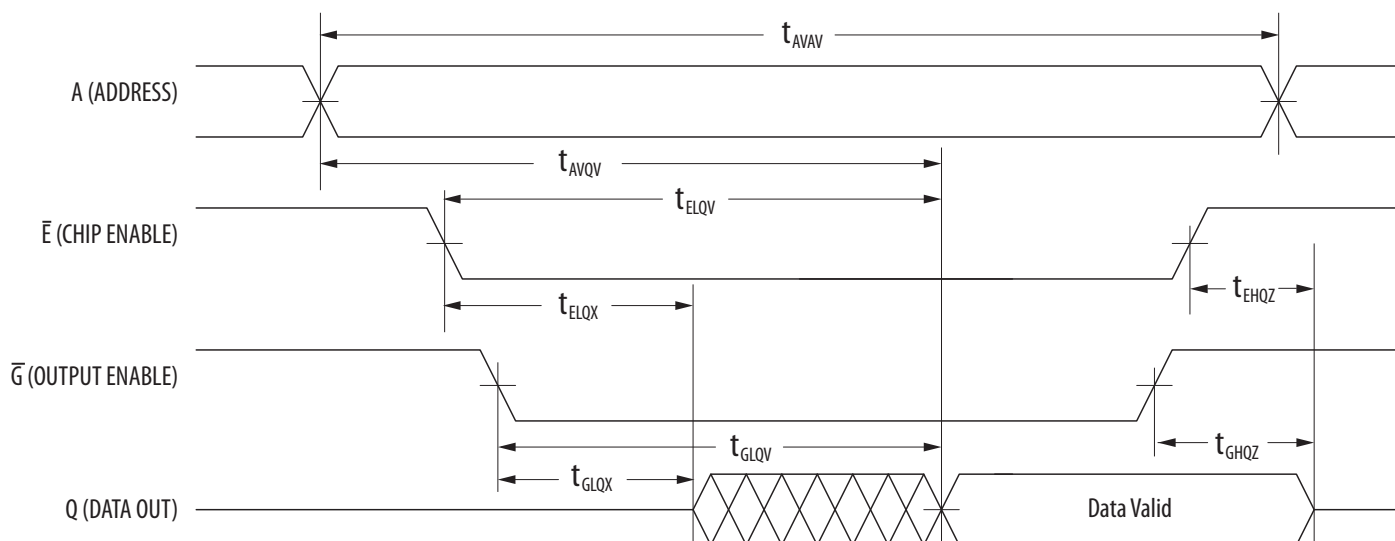
1.  $\overline{W}$  is high for read cycle. Power supplies must be properly grounded and decoupled, and bus contention conditions must be minimized or eliminated during read or write cycles.
2. Addresses valid before or at the same time  $\overline{E}$  goes low.
3. This parameter is sampled and not 100% tested. Transition is measured  $\pm 200$  mV from the steady-state voltage.

**Figure 6 – Read Cycle 1**



Note: Device is continuously selected ( $\bar{E} \leq V_{IL}$ ,  $\bar{G} \leq V_{IL}$ ).

**Figure 7 – Read Cycle 2**



## Write Mode

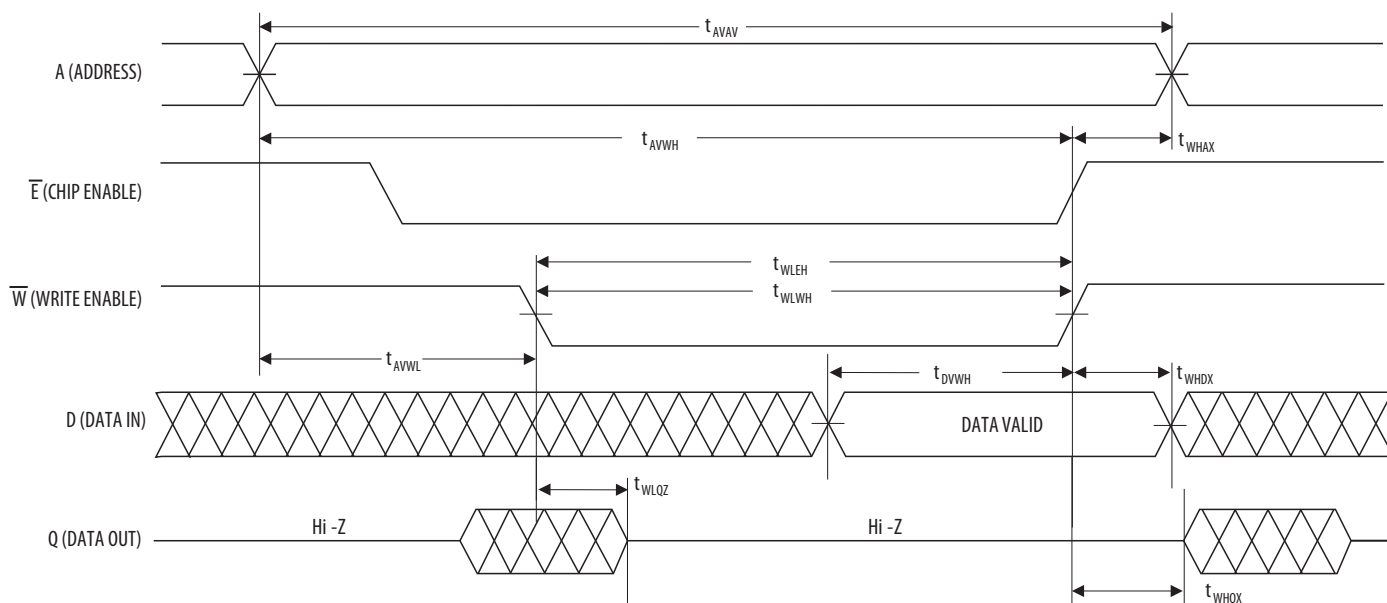
**Table 10 – Write Cycle Timing 1 (  $\overline{W}$  Controlled )**

Parameter <sup>1</sup>	Symbol	Min	Max	Unit
Write cycle time <sup>2</sup>	$t_{AVAV}$	35	-	ns
Address set-up time	$t_{AVWL}$	0	-	ns
Address valid to end of write ( $\overline{G}$ high)	$t_{AVWH}$	18	-	ns
Address valid to end of write ( $\overline{G}$ low)	$t_{AVWH}$	20	-	ns
Write pulse width ( $\overline{G}$ high)	$t_{WLWH}$ $t_{WLEH}$	15	-	ns
Write pulse width ( $\overline{G}$ low)	$t_{WLWH}$ $t_{WLEH}$	15	-	ns
Data valid to end of write	$t_{DVWH}$	10	-	ns
Data hold time	$t_{WHDX}$	0	-	ns
Write low to data Hi-Z <sup>3</sup>	$t_{WLQZ}$	0	12	ns
Write high to output active <sup>3</sup>	$t_{WHQX}$	3	-	ns
Write recovery time	$t_{WHAX}$	12	-	ns

Notes:

1. All write occurs during the overlap of  $\overline{E}$  low and  $\overline{W}$  low. Power supplies must be properly grounded and decoupled and bus contention conditions must be minimized or eliminated during read and write cycles. If  $\overline{G}$  goes low at the same time or after  $\overline{W}$  goes low, the output will remain in a high impedance state. After  $\overline{W}$  or  $\overline{E}$  has been brought high, the signal must remain in steady-state high for a minimum of 2 ns. The minimum time between  $\overline{E}$  being asserted low in one cycle to  $\overline{E}$  being asserted low in a subsequent cycle is the same as the minimum cycle time allowed for the device.
2. All write cycle timings are referenced from the last valid address to the first transition address.
3. This parameter is sampled and not 100% tested. Transition is measured  $\pm 200$  mV from the steady-state voltage. At any given voltage or temperature,  $t_{WLQZ}(\text{max}) < t_{WHQX}(\text{min})$

**Figure 8 – Write Cycle Timing 1 ( $\overline{W}$  Controlled)**



**Table 11 – Write Cycle Timing 2 ( $\bar{E}$  Controlled)**

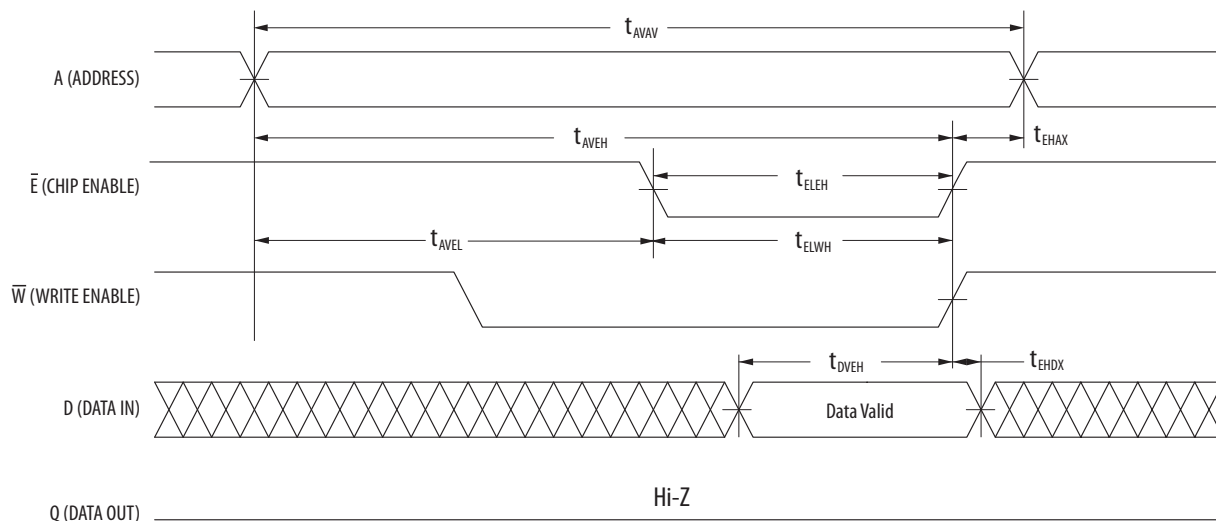
Parameter <sup>1</sup>	Symbol	Min	Max	Unit
Write cycle time <sup>2</sup>	$t_{AVAV}$	35	-	ns
Address set-up time	$t_{AVEL}$	0	-	ns
Address valid to end of write ( $\bar{G}$ high)	$t_{AVEH}$	18	-	ns
Address valid to end of write ( $\bar{G}$ low)	$t_{AVEH}$	20	-	ns
Enable to end of write ( $\bar{G}$ high)	$t_{ELEH}$ $t_{ELWH}$	15	-	ns
Enable to end of write ( $\bar{G}$ low) <sup>3</sup>	$t_{ELEH}$ $t_{ELWH}$	15	-	ns
Data valid to end of write	$t_{DVEH}$	10	-	ns
Data hold time	$t_{EHDH}$	0	-	ns
Write recovery time	$t_{EHAX}$	12	-	ns

Notes:

1. All write occurs during the overlap of  $\bar{E}$  low and  $\bar{W}$  low. Power supplies must be properly grounded and decoupled and bus contention conditions must be minimized or eliminated during read and write cycles. If  $\bar{G}$  goes low at the same time or after  $\bar{W}$  goes low, the output will remain in a high impedance state. After  $\bar{W}$  or  $\bar{E}$  has been brought high, the signal must remain in steady-state high for a minimum of 2 ns. The minimum time between  $\bar{E}$  being asserted low in one cycle to  $\bar{E}$  being asserted low in a subsequent cycle is the same as the minimum cycle time allowed for the device.
2. All write cycle timings are referenced from the last valid address to the first transition address.
3. If  $\bar{E}$  goes low at the same time or after  $\bar{W}$  goes low, the output will remain in a high-impedance state. If  $\bar{E}$  goes high at the same time or before  $\bar{W}$  goes high, the output will remain in a high-impedance state.



**Figure 9 – Write Cycle Timing 2 ( $\bar{E}$  Controlled)**



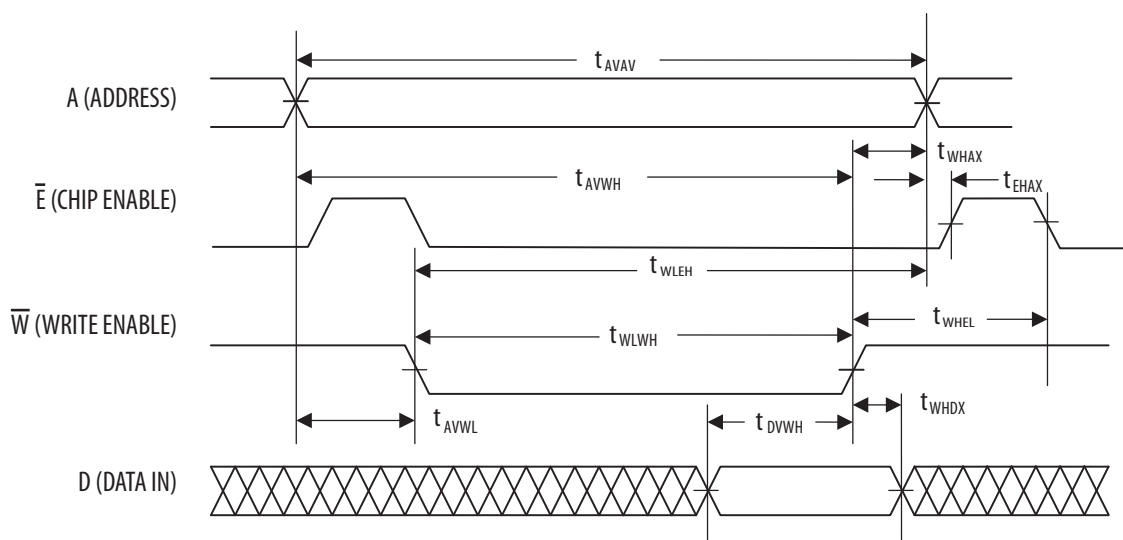
**Table 12 – Write Cycle Timing 3 (Shortened  $t_{WHAX}$ ,  $\overline{W}$  and  $\overline{E}$  Controlled)**

Parameter <sup>1</sup>	Symbol	Min	Max	Unit
Write cycle time <sup>2</sup>	$t_{AVAV}$	35	-	ns
Address set-up time	$t_{AVWL}$	0	-	ns
Address valid to end of write ( $\overline{G}$ high)	$t_{AVWH}$	18	-	ns
Address valid to end of write ( $\overline{G}$ low)	$t_{AVWH}$	20	-	ns
Write pulse width	$t_{WLWH}$ $t_{WLEH}$	15	-	ns
Data valid to end of write	$t_{DVWH}$	10	-	ns
Data hold time	$t_{WHDX}$	0	-	ns
Enable recovery time	$t_{EHAX}$	-2	-	ns
Write recovery time <sup>3</sup>	$t_{WHAX}$	6	-	ns
Write to enable recovery time <sup>3</sup>	$t_{WHEL}$	12	-	ns

Notes:

1. All write occurs during the overlap of  $\overline{E}$  low and  $\overline{W}$  low. Power supplies must be properly grounded and decoupled and bus contention conditions must be minimized or eliminated during read and write cycles. If  $\overline{G}$  goes low at the same time or after  $\overline{W}$  goes low, the output will remain in a high impedance state. After  $\overline{W}$ , or  $\overline{E}$  has been brought high, the signal must remain in steady-state high for a minimum of 2 ns. The minimum time between  $\overline{E}$  being asserted low in one cycle to  $\overline{E}$  being asserted low in a subsequent cycle is the same as the minimum cycle time allowed for the device.
2. All write cycle timings are referenced from the last valid address to the first transition address.
3. If  $\overline{E}$  goes low at the same time or after  $\overline{W}$  goes low the output will remain in a high impedance state. If  $\overline{E}$  goes high at the same time or before  $\overline{W}$  goes high the output will remain in a high impedance state.  $\overline{E}$  must be brought high each cycle.

**Figure 10 – Write Cycle Timing 3 (Shortened  $t_{WHAX}$ ,  $\overline{W}$  and  $\overline{E}$  Controlled)**



## ORDERING INFORMATION

**Table 13 – Ordering Part Number System for Parallel I/O MRAM**

Example Ordering Part Number			Memory	Density	Type	I/O Width	Rev.	Temp	Package	Speed	Packing	Grade
MRAM	MR		MR	0	A	08	B	C	MA	35	R	
256 Kb	256											
1 Mb	0											
4 Mb	2											
16 Mb	4											
Async 3.3v	A											
Async 3.3v Vdd and 1.8v Vddq	D											
Async 3.3v Vdd and 1.8v Vddq with 2.7v min. Vdd	DL											
8-bit	08											
16-bit	16											
Rev A	A											
Rev B	B											
Commercial	0 to 70°C	Blank										
Industrial	-40 to 85°C	C										
Extended	-40 to 105°C	V										
AEC Q-100 Grade 1	-40 to 125°C	M										
44-TSOP-2	YS											
48-FBGA	MA											
16-SOIC	SC											
32-SOIC	SO											
35 ns	35											
45 ns	45											
Tray	Blank											
Tape and Reel	R											
Engineering Samples	ES											
Customer Samples	Blank											
Mass Production	Blank											

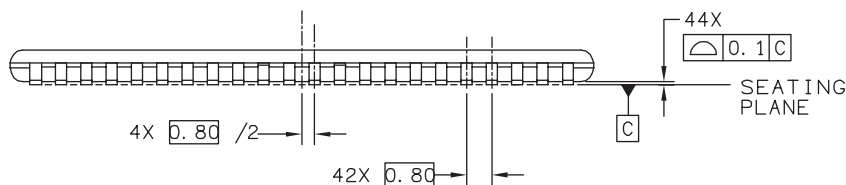
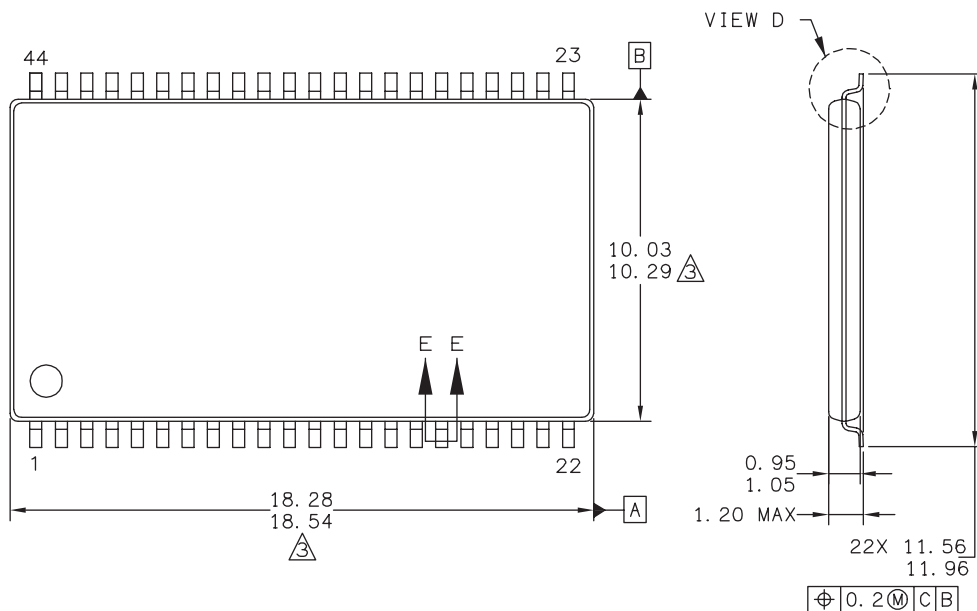
**Table 14 – MR0A08B Ordering Part Numbers <sup>1</sup>**

Temp Grade	Temp	Package	Shipping	Ordering Part Number
Commercial	0 to +70 °C	44-TSOP2	Tray	MR0A08BYS35
			Tape and Reel	MR0A08BYS35R
		48-BGA	Tray	MR0A08BMA35
			Tape and Reel	MR0A08BMA35R
		32-SOIC <sup>1</sup>	Tray	MR0A08BSO35 Obsolete
			Tape and Reel	MR0A08BSO35R Obsolete
Industrial	-40 to +85 °C	44-TSOP2	Tray	MR0A08BCYS35
			Tape and Reel	MR0A08BCYS35R
		48-BGA	Tray	MR0A08BCMA35
			Tape and Reel	MR0A08BCMA35R
		32-SOIC <sup>1</sup>	Tray	MR0A08BCSO35 Obsolete
			Tape and Reel	MR0A08BCSO35R Obsolete

<sup>1</sup> The 32-SOIC package option is obsolete and no longer available. See PCN02895 here.

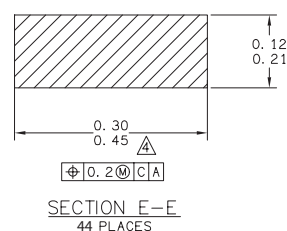
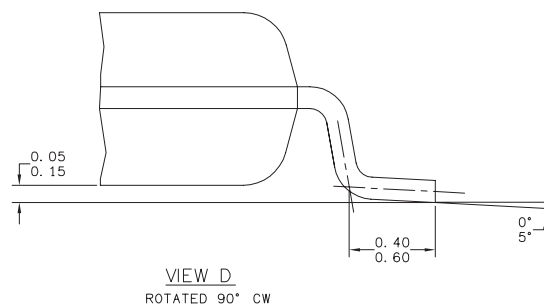
## PACKAGE OUTLINE DRAWINGS

**Figure 11 – 44-TSOP2 Package Outline**

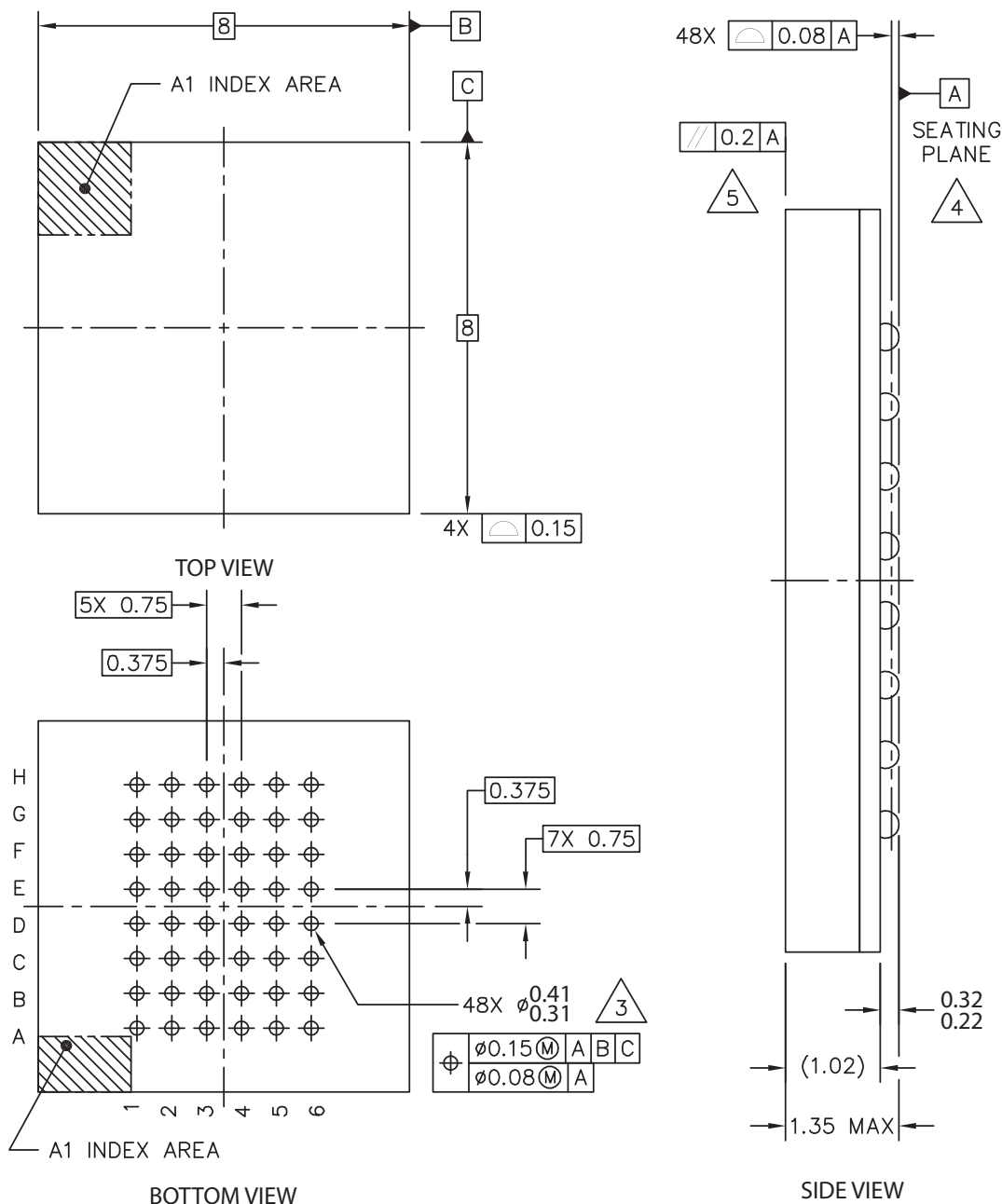


### Not To Scale

1. Dimensions and tolerances per ASME Y14.5M - 1994.
2. Dimensions in Millimeters.
3. Dimensions do not include mold protrusion.
4. Dimension does not include DAM bar protrusions.
5. DAM Bar protrusion shall not cause the lead width to exceed 0.58.



**Figure 12 – 48-BGA Package Outline**



**Not To Scale**

1. Dimensions in Millimeters.

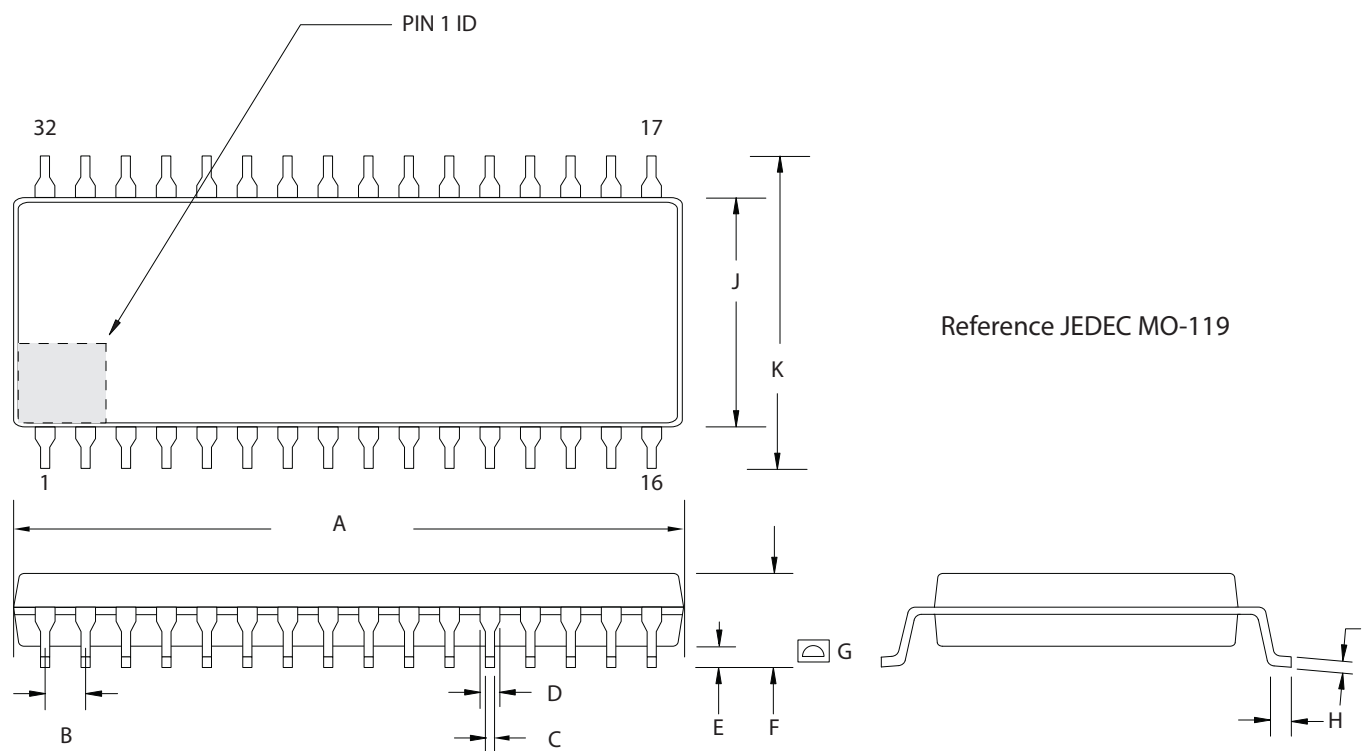
2. Dimensions and tolerances per ASME Y14.5M - 1994.

3. Maximum solder ball diameter measured parallel to DATUM A

4. DATUM A, the seating plane is determined by the spherical crowns of the solder balls.

5. Parallelism measurement shall exclude any effect of mark on top surface of package.

**Figure 13 – 32-SOIC Package Outline <sup>1</sup>**



Unit	A	B	C	D	E	F	G	H	I	J	K
mm - Min	20.574	1.00	0.355	0.66	0.101	2.286	Radius	0.533	0.152	7.416	10.287
- Max	20.878	1.50	0.508	0.81	0.254	2.540	0.101	1.041	0.304	7.594	10.642
inch - Min	0.810	0.04	0.14	0.026	0.004	0.09	Radius	0.021	0.006	0.292	0.405
- Max	0.822	0.06	0.02	0.032	0.010	0.10	0.0040	0.041	0.012	0.299	0.419

**Note:**

1. The 32-SOIC package is obsolete and shown for legacy reference only. This package option is no longer available for new orders.

## REVISION HISTORY

Revision	Date	Description of Change
0	Sep 12, 2008	Initial Advance Information Release
1	May 8, 2009	Revised format; Add Table 3.6 Write Timing Cycle 3; Add Figure 3.6 Write Timing Cycle 3; Add TSOPII Lead Width Info; Changed to Preliminary from Product Concept.
2	June 18, 2009	Changed from datasheet from Preliminary to Production except where noted.
3	Apr 12, 2011	Added SOIC package option.
4	August 15, 2011	Corrected SOIC Pin 1 to read DC. Updated contact information. Revised copyright year.
5	Dec 16, 2011	Changed TSOP-II to TSOP2. Changed logo to new EST Logo. Added Industrial Temp Grade option in SOIC package, Table 4.1. Deleted Tape & Reel pack option for all SOIC packaged parts. Figure 2.1 cosmetic update. Figure 5.2 BGA package outline drawing revised for ball size.
6	July 9, 2013	MR0A08BCSO35 preliminary status removed. Now MP.
7	September 4, 2013	Added table of dimensions to the SOIC package outline diagram.
8	October 11, 2013	Added Tape and Reel shipping option for SOIC packaged versions. Reformatted to current standards.
8.1	May 18, 2015	Revised How to Contact Us information.
8.2	June 11, 2015	Correction to Japan Sales Office telephone number.
8.3	July 20, 2015	32-SOIC package options Not Recommended for New Designs.
8.4	October 17, 2015	32-SOIC package options are obsolete and no longer available.
8.5	December 9, 2015	Corrections to incorrect package pinouts and replaced missing 48-BGA package outline drawing.

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